

# COMPLEMENTARY SILICON POWER TRANSISTORS

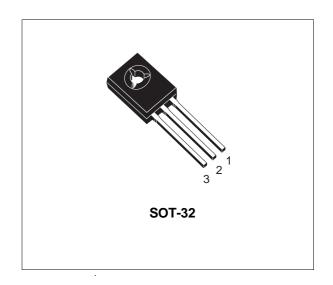
- STMicroelectronics PREFERRED SALESTYPE
- COMPLEMENTARY PNP NPN DEVICES

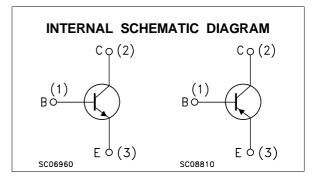
### **DESCRIPTION**

The BD433, BD435, and BD437 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package, intented for use in medium power linear and switching applications.

The BD433 is especially suitable for use in car-radio output stages.

The complementary PNP types are BD434, BD436, and BD438 respectively.





## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter			Value		Unit
		NPN	BD433	BD435	BD437	
		PNP	BD434	BD436	BD438	
V <sub>CBO</sub>	Collector-Base Voltage (I <sub>E</sub> = 0)	·	22	32	45	V
Vces	Collector-Emitter Voltage (V <sub>BE</sub> = 0)		22	32	45	V
$V_{CEO}$	Collector-Emitter Voltage (I <sub>B</sub> = 0)		22	32	45	V
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)			5		V
Ic	Collector Current			4		Α
$I_{CM}$	Collector Peak Current (t ≤ 10 ms)			7		Α
Ι <sub>Β</sub>	Base Current			1		Α
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> ≤ 25 °C			36		W
$T_{stg}$	Storage Temperature			-65 to 150		°C
Tj	Max. Operating Junction Temperature			150		°C

For PNP types voltage and current values are negative.

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## BD433 BD434 BD435 BD436 BD437 BD438

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	3.5	°C/W	
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	100	°C/W	

## **ELECTRICAL CHARACTERISTICS** ( $T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

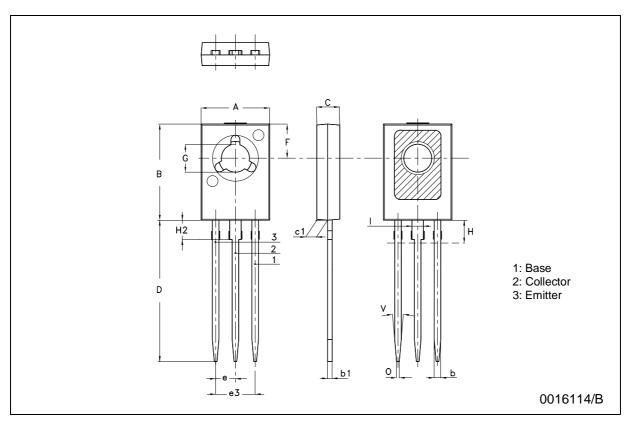
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I <sub>E</sub> = 0)	for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>	$V_{CB} = 32 \text{ V}$			100 100 100	μΑ μΑ μΑ
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>	$V_{CE} = 32 \text{ V}$			100 100 100	μΑ μΑ μΑ
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V				1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>	22 32 45			V V V
VCE(sat)*	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2 A	I <sub>B</sub> = 0.2 A for <b>BD433/434</b> for <b>BD435/436</b> for <b>BD437/438</b>		0.2 0.2 0.2	0.5 0.5 0.6	V V V
V <sub>BE</sub> *	Base-Emitter Voltage	I <sub>C</sub> = 10 mA I <sub>C</sub> = 2 A	$V_{CE} = 5 \text{ V}$ $V_{CE} = 1 \text{ V}$ for BD433/434 for BD435/436 for BD437/438		0.58	1.1 1.1 1.2	V V V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 10 mA I <sub>C</sub> = 500 mA I <sub>C</sub> = 2 A	VCE = 5 V for BD433/434 for BD435/436 for BD437/438 VCE = 1 V VCE = 1 V for BD433/434 for BD435/436	40 40 30 85 50 50 40	130 130 130 140		
h <sub>FE1</sub> /h <sub>FE2</sub> *	Matched Pair	I <sub>C</sub> = 500 mA	V <sub>CE</sub> = 1 V			1.4	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> = 250 mA	V <sub>CE</sub> = 1 V	3			MHz

<sup>\*</sup> Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

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# SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	7.4		7.8	0.291		0.307	
В	10.5		10.8	0.413		0.425	
b	0.7		0.9	0.028		0.035	
b1	0.40		0.65	0.015		0.025	
С	2.4		2.7	0.094		0.106	
c1	1.0		1.3	0.039		0.051	
D	15.4		16.0	0.606		0.630	
е		2.2			0.087		
e3		4.4			0.173		
F		3.8			0.150		
G	3		3.2	0.118		0.126	
Н			2.54			0.100	
H2		2.15			0.084		
!		1.27			0.05		
0		0.3			0.011		
V		10°			10°		



#### BD433 BD434 BD435 BD436 BD437 BD438

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